



## TO-3P Plastic-Encapsulate Transistors

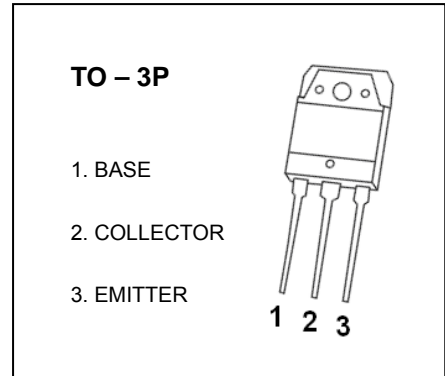
### 2SB688 TRANSISTOR (PNP)

#### FEATURES

- High Breakdown Voltage
- Complement to Type 2SD718

#### APPLICATIONS

- Power Amplifier Applications



#### MAXIMUM RATINGS ( $T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-Base Voltage	-120	V
$V_{CEO}$	Collector-Emitter Voltage	-120	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current	-8	A
$P_C$	Collector Power Dissipation	3	W
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	42	$^{\circ}\text{C}/\text{W}$
$T_j$	Junction Temperature	150	$^{\circ}\text{C}$
$T_{stg}$	Storage Temperature	-55~+150	$^{\circ}\text{C}$

#### ELECTRICAL CHARACTERISTICS ( $T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu\text{A}, I_E=0$	-120			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}^*$	$I_C=-50\text{mA}, I_B=0$	-120			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu\text{A}, I_C=0$	-5			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=-120\text{V}, I_E=0$			-10	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=-5\text{V}, I_C=0$			-10	$\mu\text{A}$
DC current gain	$h_{FE}^*$	$V_{CE}=-5\text{V}, I_C=-1\text{A}$	55		160	
Collector-emitter saturation voltage	$V_{CE(sat)}^*$	$I_C=-5\text{A}, I_B=-500\text{mA}$			-2.5	V
Base-emitter voltage	$V_{BE}^*$	$V_{CE}=-5\text{V}, I_C=-5\text{A}$			-1.5	V
Collector output capacitance	$C_{ob}$	$V_{CB}=-10\text{V}, I_E=0, f=1\text{MHz}$		280		pF
Transition frequency	$f_T$	$V_{CE}=-5\text{V}, I_C=-1\text{A}, f=1\text{MHz}$		10		MHz

\*Pulse test

#### CLASSIFICATION OF $h_{FE}$

RANK	R	O
RANGE	55-110	80-160